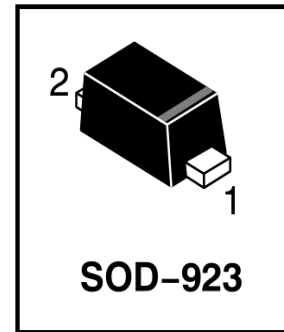


SEB521CS-30
Schottky barrier diode

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Low current rectification
- Low VF
- High reliability.
- Silicon epitaxial planar



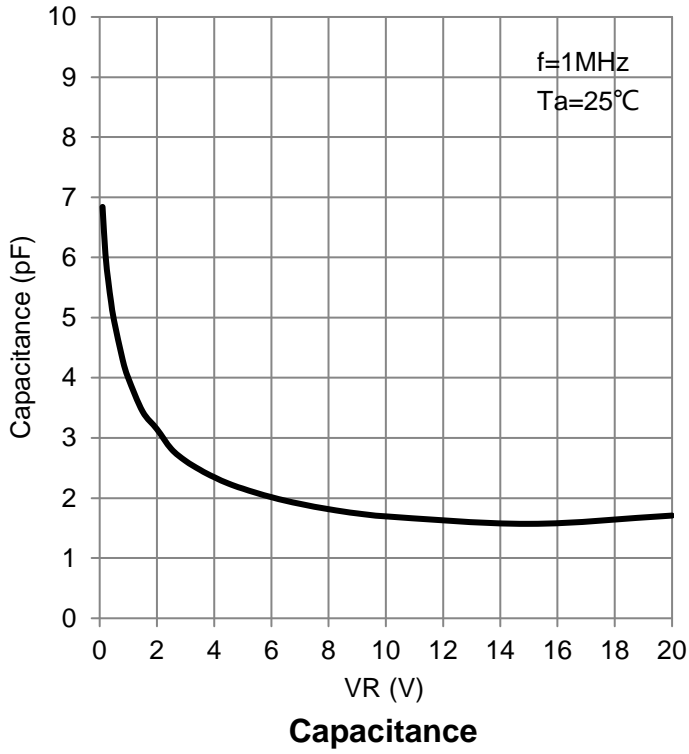
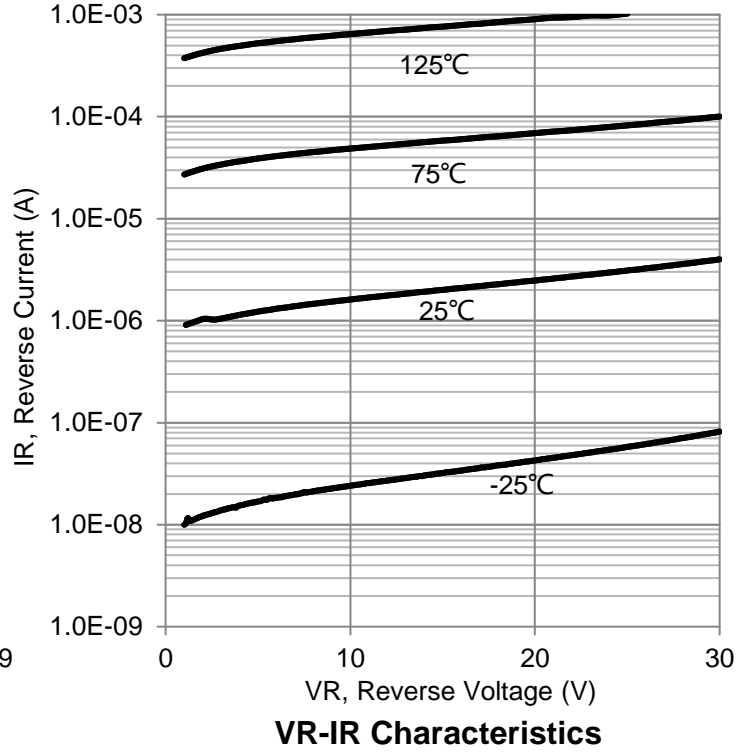
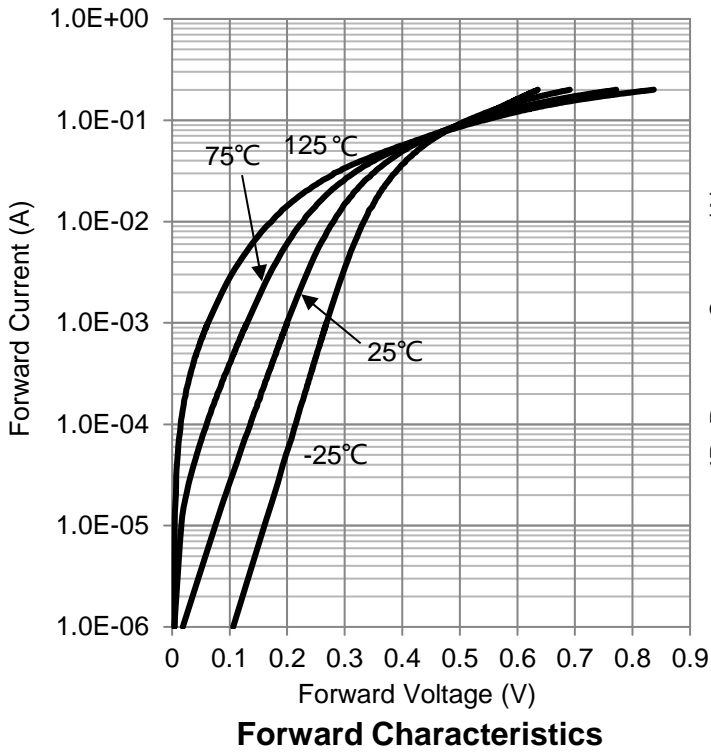
2. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	VR	30	V
Average rectifier forward current	IO	100	mA
Forward current surge peak(60Hz · 1cyc)	IFSM	500	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-40~+125	°C

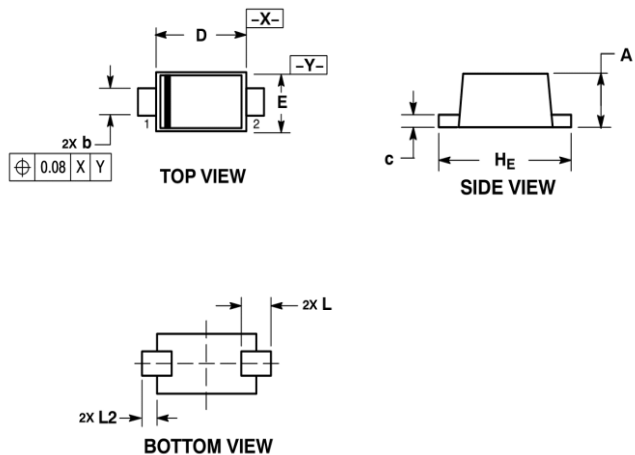
3. ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Forward voltage (IF =10mA)	VF	-	-	0.35	V
(IF =20mA)				0.4	
Reverse current (VR =10V)	IR	-	-	10	μA

4.ELECTRICAL CHARACTERISTICS CURVES



5.OUTLINE AND DIMENSIONS

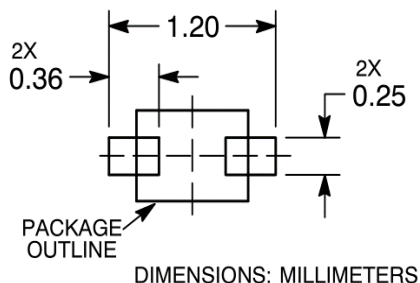


Notes:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.34	0.37	0.40	0.013	0.015	0.016
b	0.15	0.20	0.25	0.006	0.008	0.010
c	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
E	0.55	0.60	0.65	0.022	0.024	0.026
HE	0.95	1.00	1.05	0.037	0.039	0.041
L	0.19REF			0.007REF		
L2	0.05	0.10	0.15	0.002	0.004	0.006

6.SOLDERING FOOTPRINT



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